

	Hits	Search Text	DBs
8	7	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (mark or alignment)) and etch\$4 and (lithograph\$6 or pattern\$4) and ((reverse or mirror) same (alignment near12 mark) same (substrate or wafer or surface or device) same trench\$4)	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
9	105	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (mark or alignment)) and etch\$4 and (lithograph\$6 or pattern\$4) and ((alignment near12 mark) same (substrate or wafer or surface) same trench\$4 same (open\$4 or reveal\$4 or show\$3))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	76	((substrate or wafer or device or platen) same (alignment near12 mark) same ((first near12 second) or (front near18 back) or (front\$4 near14 rear\$4))) and (((protective near5 layer) or (insulat\$4 near9 layer) or SiO\$3 or (silicon near6 \$4oxide)) same (mark or alignment)) and etch\$4 and (lithograph\$6 or pattern\$4) and (((open\$4 or reveal\$4 or show\$3) near12 (alignment near12 mark)) same (substrate or wafer or surface) same trench\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB